

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM850-251CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 83.32 V/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

E-field emissions = 183.8 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

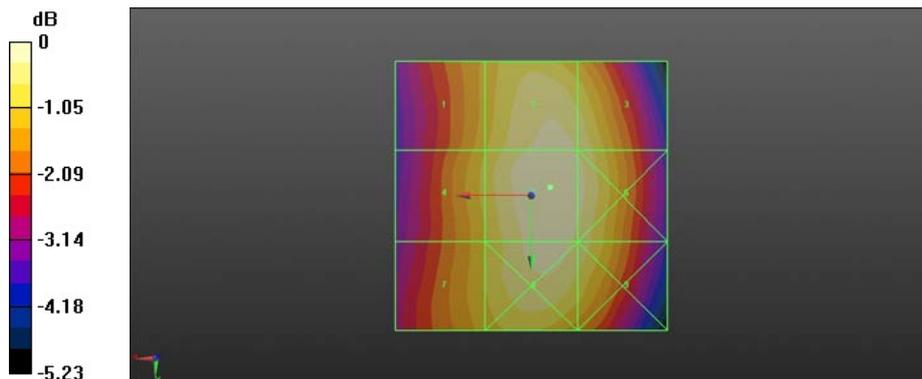
Grid 1 M3 162.3 V/m	Grid 2 M3 180.2 V/m	Grid 3 M3 176.1 V/m
Grid 4 M3 165.6 V/m	Grid 5 M3 183.8 V/m	Grid 6 M3 179.3 V/m
Grid 7 M3 163.0 V/m	Grid 8 M3 180.4 V/m	Grid 9 M3 175.2 V/m

Cursor:

Total = 183.8 V/m

E Category: M3

Location: -3.5, -1.5, 8.7 mm



0 dB = 183.8 V/m = 45.29 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM850-190CH**DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 92.99 V/m; Power Drift = 0.05 dB

PMF = 2.830 is applied.

E-field emissions = 206.3 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

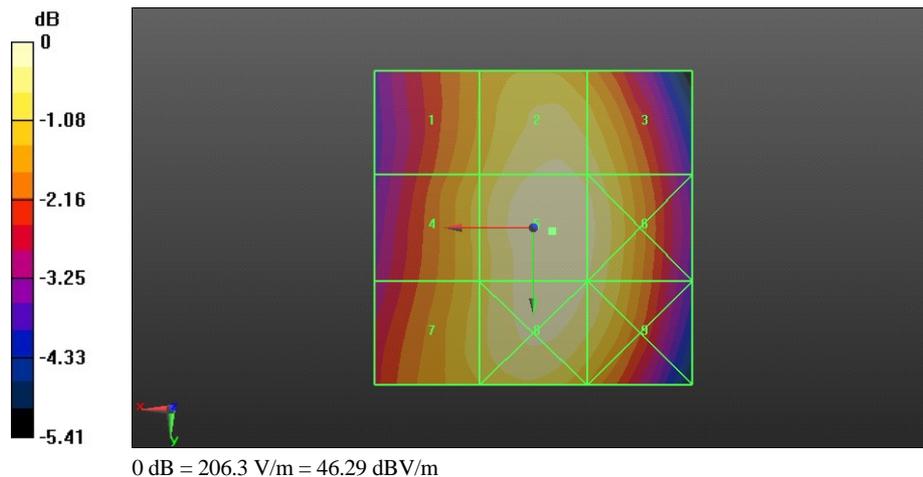
Grid 1 M3 181.2 V/m	Grid 2 M3 200.4 V/m	Grid 3 M3 195.2 V/m
Grid 4 M3 186.2 V/m	Grid 5 M3 206.3 V/m	Grid 6 M3 200.9 V/m
Grid 7 M3 187.0 V/m	Grid 8 M3 203.8 V/m	Grid 9 M3 197.9 V/m

Cursor:

Total = 206.3 V/m

E Category: M3

Location: -3, 0.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM850-128CH**DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 101.2 V/m; Power Drift = 0.02 dB

PMF = 2.830 is applied.

E-field emissions = 222.5 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

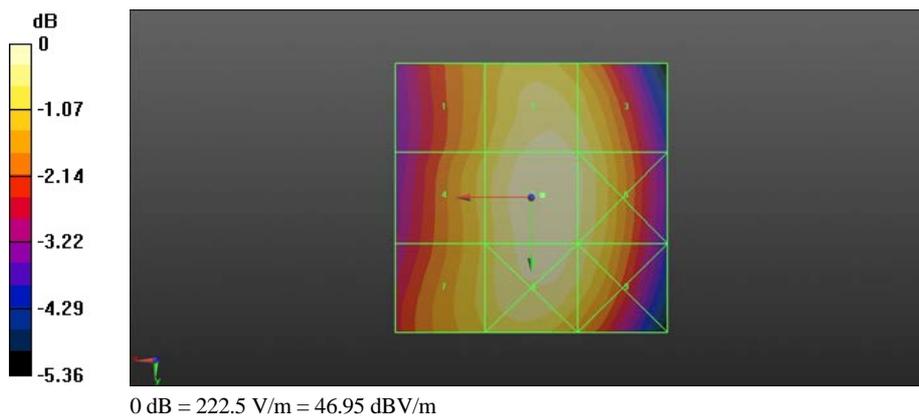
Grid 1 M3 196.2 V/m	Grid 2 M3 217.7 V/m	Grid 3 M3 212.3 V/m
Grid 4 M3 201.8 V/m	Grid 5 M3 222.5 V/m	Grid 6 M3 215.9 V/m
Grid 7 M3 200.7 V/m	Grid 8 M3 219.3 V/m	Grid 9 M3 211.8 V/m

Cursor:

Total = 222.5 V/m

E Category: M3

Location: -2, -0.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM850-128CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 103.1 V/m; Power Drift = -0.08 dB

PMF = 2.830 is applied.

E-field emissions = 223.9 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

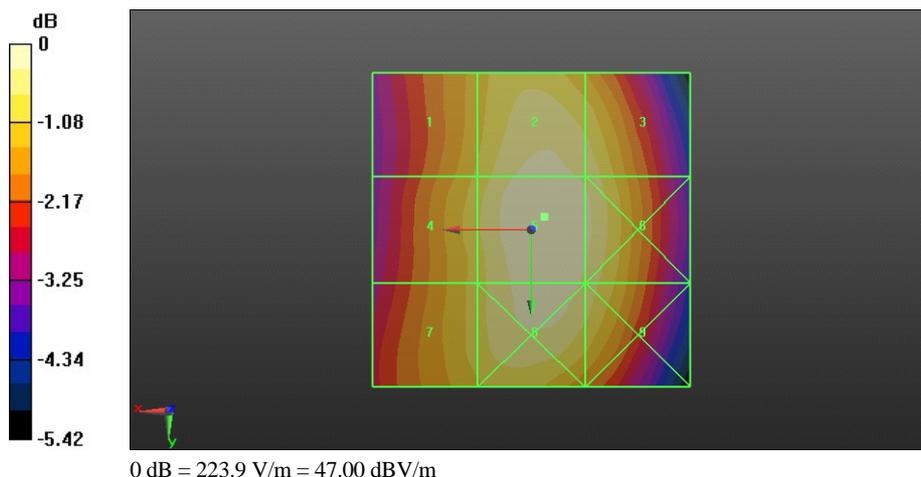
Grid 1 M3 199.7 V/m	Grid 2 M3 219.0 V/m	Grid 3 M3 212.8 V/m
Grid 4 M3 204.6 V/m	Grid 5 M3 223.9 V/m	Grid 6 M3 217.4 V/m
Grid 7 M3 202.3 V/m	Grid 8 M3 220.5 V/m	Grid 9 M3 212.6 V/m

Cursor:

Total = 223.9 V/m

E Category: M3

Location: -2, -2, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM850-251CH**DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 848.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06600 A/m; Power Drift = 0.02 dB

PMF = 2.820 is applied.

H-field emissions = 0.2593 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

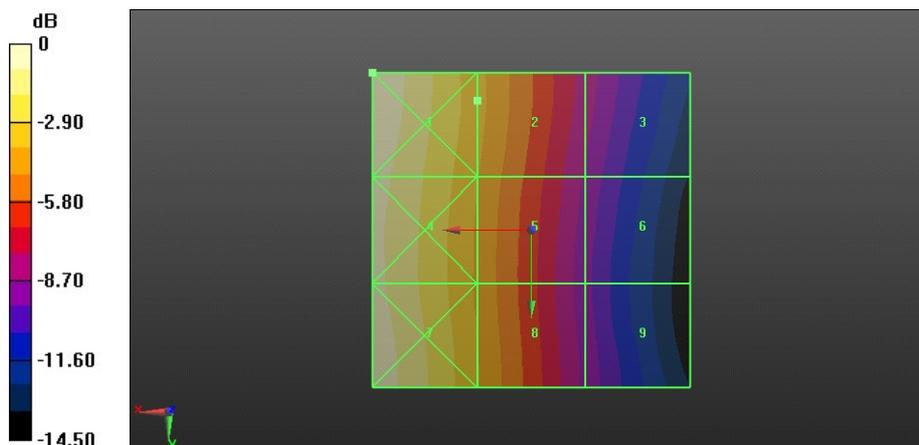
Grid 1 M4 0.388 A/m	Grid 2 M4 0.259 A/m	Grid 3 M4 0.152 A/m
Grid 4 M4 0.367 A/m	Grid 5 M4 0.250 A/m	Grid 6 M4 0.141 A/m
Grid 7 M4 0.377 A/m	Grid 8 M4 0.251 A/m	Grid 9 M4 0.138 A/m

Cursor:

Total = 0.3876 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.3876 A/m = -8.23 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM850-190CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 836.6 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07300 A/m; Power Drift = 0.01 dB

PMF = 2.820 is applied.

H-field emissions = 0.2923 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

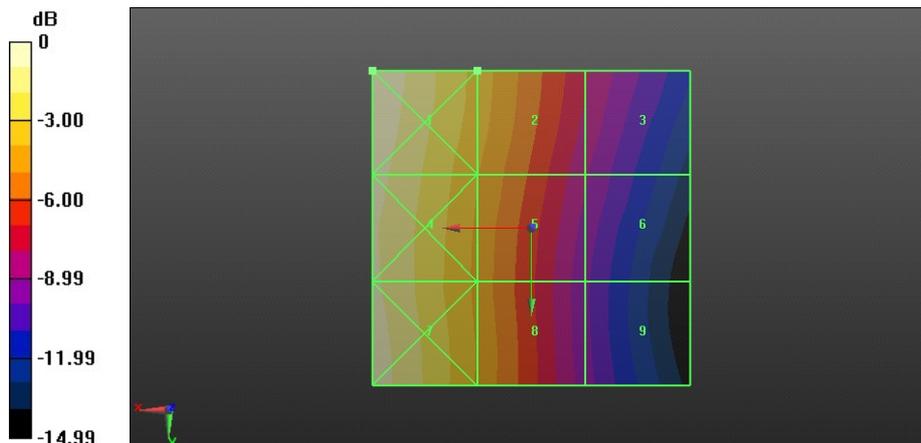
Grid 1 M4 0.431 A/m	Grid 2 M4 0.292 A/m	Grid 3 M4 0.176 A/m
Grid 4 M4 0.405 A/m	Grid 5 M4 0.275 A/m	Grid 6 M4 0.156 A/m
Grid 7 M4 0.410 A/m	Grid 8 M4 0.270 A/m	Grid 9 M4 0.145 A/m

Cursor:

Total = 0.4309 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.4309 A/m = -7.31 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM850-128CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08000 A/m; Power Drift = 0.01 dB

PMF = 2.820 is applied.

H-field emissions = 0.3086 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

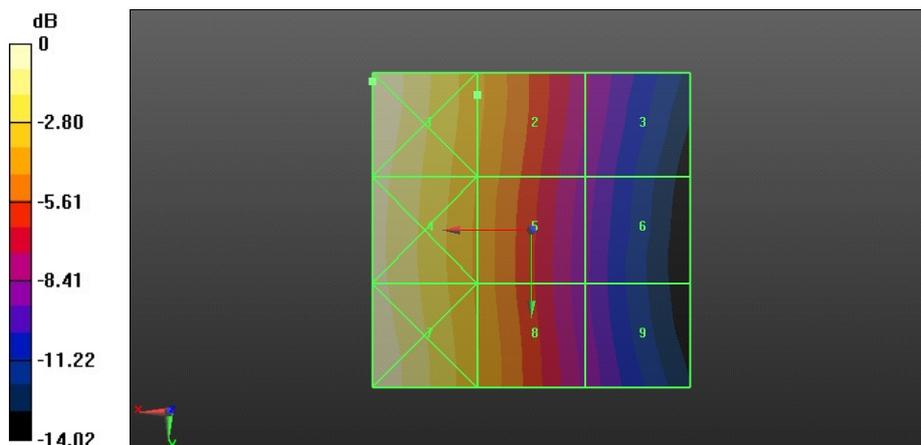
Grid 1 M3 0.459 A/m	Grid 2 M4 0.309 A/m	Grid 3 M4 0.179 A/m
Grid 4 M4 0.435 A/m	Grid 5 M4 0.298 A/m	Grid 6 M4 0.167 A/m
Grid 7 M3 0.456 A/m	Grid 8 M4 0.302 A/m	Grid 9 M4 0.170 A/m

Cursor:

Total = 0.4589 A/m

H Category: M3

Location: 25, -23.5, 8.7 mm



0 dB = 0.4589 A/m = -6.76 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM850-128CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 824.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07900 A/m; Power Drift = -0.04 dB

PMF = 2.820 is applied.

H-field emissions = 0.3051 A/m

Near-field category: M4 (AWF -5 dB)

PMF scaled H-field

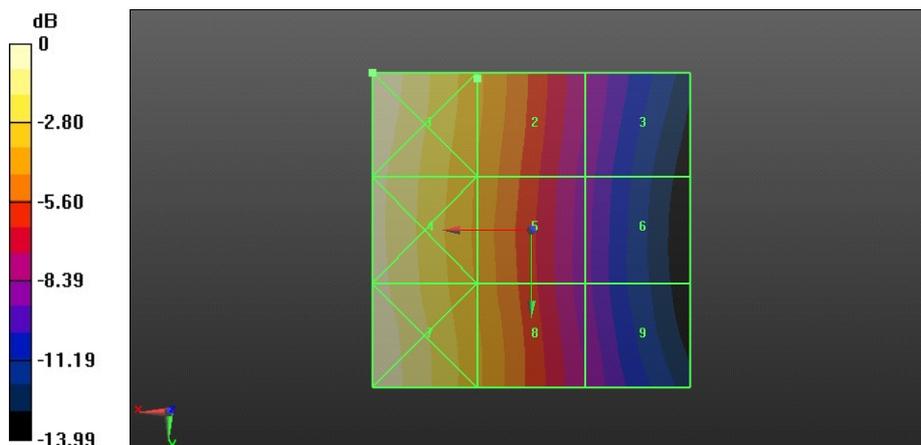
Grid 1 M3 0.455 A/m	Grid 2 M4 0.305 A/m	Grid 3 M4 0.177 A/m
Grid 4 M4 0.430 A/m	Grid 5 M4 0.293 A/m	Grid 6 M4 0.165 A/m
Grid 7 M3 0.452 A/m	Grid 8 M4 0.304 A/m	Grid 9 M4 0.174 A/m

Cursor:

Total = 0.4551 A/m

H Category: M3

Location: 25, -25, 8.7 mm



0 dB = 0.4551 A/m = -6.84 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM1900-810CH**DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1**

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz; Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 17.22 V/m; Power Drift = -0.04 dB

PMF = 2.860 is applied.

E-field emissions = 53.93 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

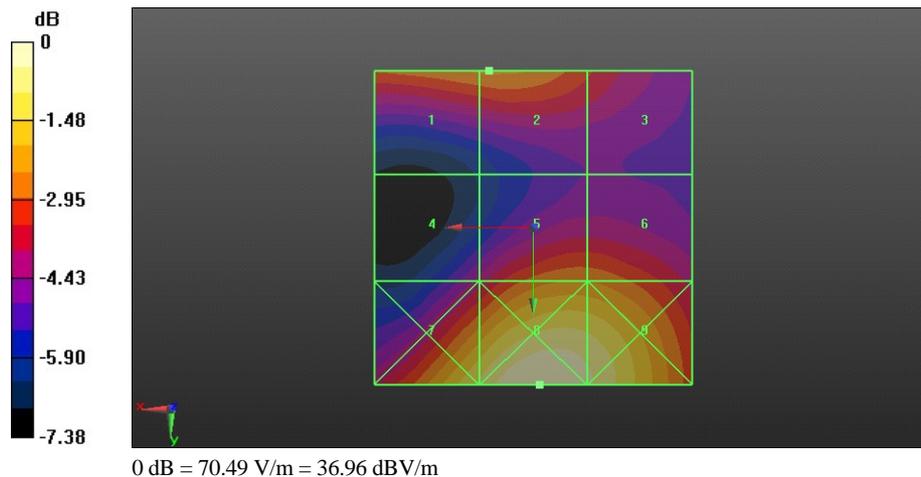
Grid 1 M3 53.77 V/m	Grid 2 M3 53.93 V/m	Grid 3 M3 48.10 V/m
Grid 4 M4 43.59 V/m	Grid 5 M3 53.31 V/m	Grid 6 M3 53.11 V/m
Grid 7 M3 64.00 V/m	Grid 8 M3 70.49 V/m	Grid 9 M3 67.43 V/m

Cursor:

Total = 70.49 V/m

E Category: M3

Location: -1, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM1900-661CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 18.18 V/m; Power Drift = 0.03 dB

PMF = 2.860 is applied.

E-field emissions = 59.80 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

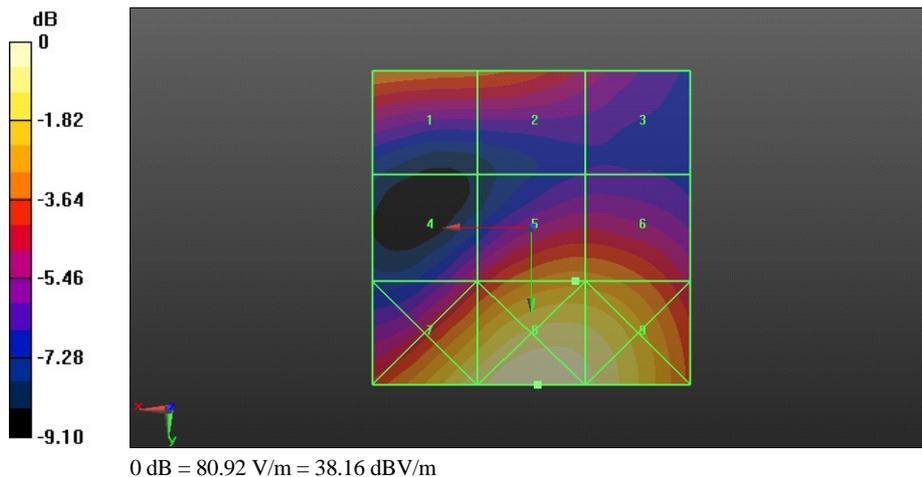
Grid 1 M3 57.81 V/m	Grid 2 M3 54.89 V/m	Grid 3 M4 45.58 V/m
Grid 4 M4 47.18 V/m	Grid 5 M3 59.80 V/m	Grid 6 M3 59.57 V/m
Grid 7 M3 74.25 V/m	Grid 8 M3 80.92 V/m	Grid 9 M3 76.91 V/m

Cursor:

Total = 80.92 V/m

E Category: M3

Location: -1, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM1900-512CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 18.27 V/m; Power Drift = -0.06 dB

PMF = 2.860 is applied.

E-field emissions = 59.67 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

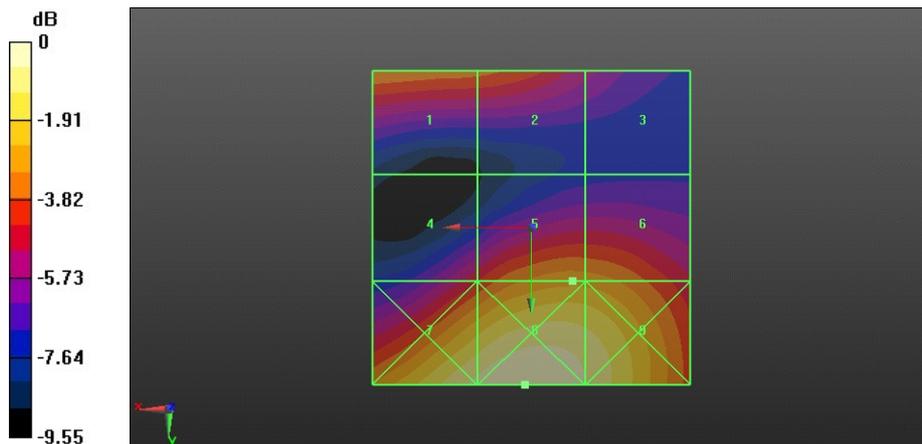
Grid 1 M3 57.22 V/m	Grid 2 M3 54.59 V/m	Grid 3 M4 43.82 V/m
Grid 4 M3 48.99 V/m	Grid 5 M3 59.67 V/m	Grid 6 M3 59.46 V/m
Grid 7 M3 77.97 V/m	Grid 8 M3 81.79 V/m	Grid 9 M3 76.00 V/m

Cursor:

Total = 81.79 V/m

E Category: M3

Location: 1, 25, 8.7 mm



0 dB = 81.79 V/m = 38.25 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-GSM1900-661CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 18.82 V/m; Power Drift = 0.02 dB

PMF = 2.860 is applied.

E-field emissions = 60.72 V/m

Near-field category: M3 (AWF -5 dB)

PMF scaled E-field

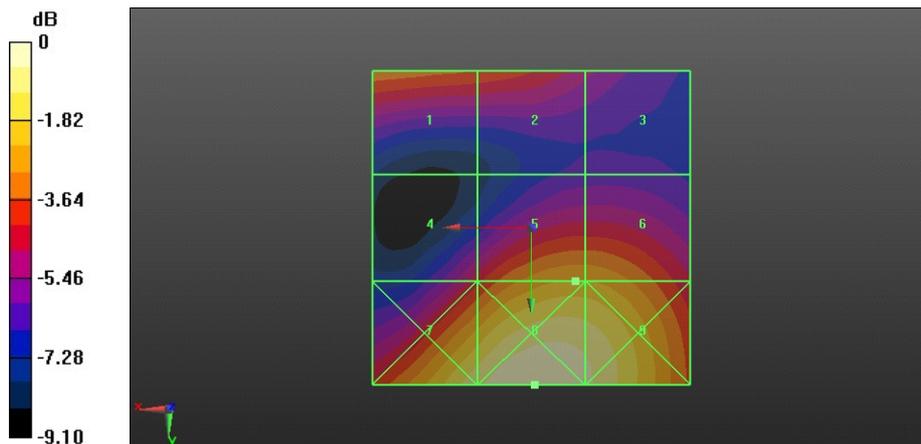
Grid 1 M3 55.57 V/m	Grid 2 M3 52.47 V/m	Grid 3 M4 43.81 V/m
Grid 4 M3 47.87 V/m	Grid 5 M3 60.72 V/m	Grid 6 M3 60.54 V/m
Grid 7 M3 73.13 V/m	Grid 8 M3 79.58 V/m	Grid 9 M3 75.36 V/m

Cursor:

Total = 79.58 V/m

E Category: M3

Location: -0.5, 25, 8.7 mm



0 dB = 79.58 V/m = 38.02 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM1900-810CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1909.8 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06300 A/m; Power Drift = 0.00 dB

PMF = 2.830 is applied.

H-field emissions = 0.1624 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

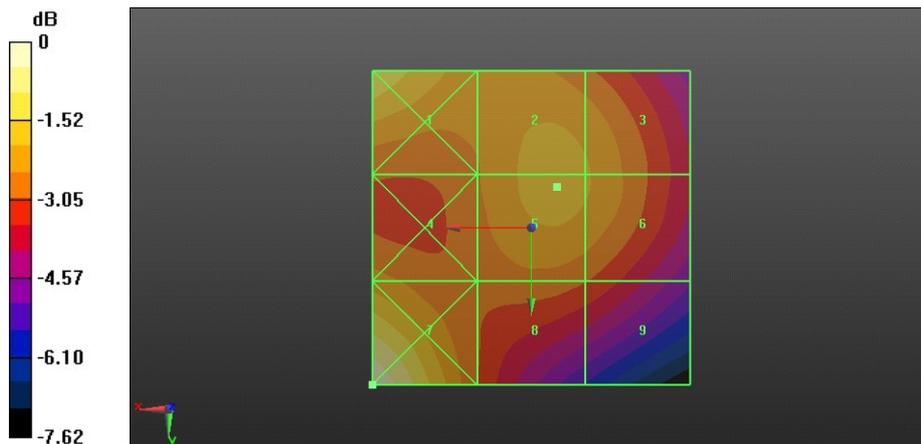
Grid 1 M3 0.180 A/m	Grid 2 M3 0.162 A/m	Grid 3 M3 0.159 A/m
Grid 4 M3 0.155 A/m	Grid 5 M3 0.162 A/m	Grid 6 M3 0.160 A/m
Grid 7 M3 0.200 A/m	Grid 8 M3 0.146 A/m	Grid 9 M3 0.141 A/m

Cursor:

Total = 0.2002 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.2002 A/m = -13.97 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM1900-661CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1880 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06800 A/m; Power Drift = -0.02 dB

PMF = 2.830 is applied.

H-field emissions = 0.1739 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

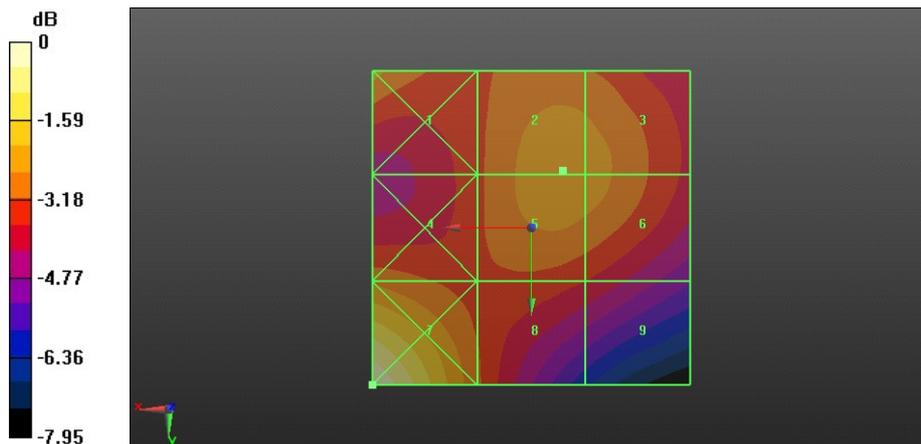
Grid 1 M3 0.173 A/m	Grid 2 M3 0.174 A/m	Grid 3 M3 0.172 A/m
Grid 4 M3 0.166 A/m	Grid 5 M3 0.174 A/m	Grid 6 M3 0.172 A/m
Grid 7 M3 0.227 A/m	Grid 8 M3 0.160 A/m	Grid 9 M3 0.148 A/m

Cursor:

Total = 0.2267 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.2267 A/m = -12.89 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM1900-512CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07300 A/m; Power Drift = 0.01 dB

PMF = 2.830 is applied.

H-field emissions = 0.1861 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

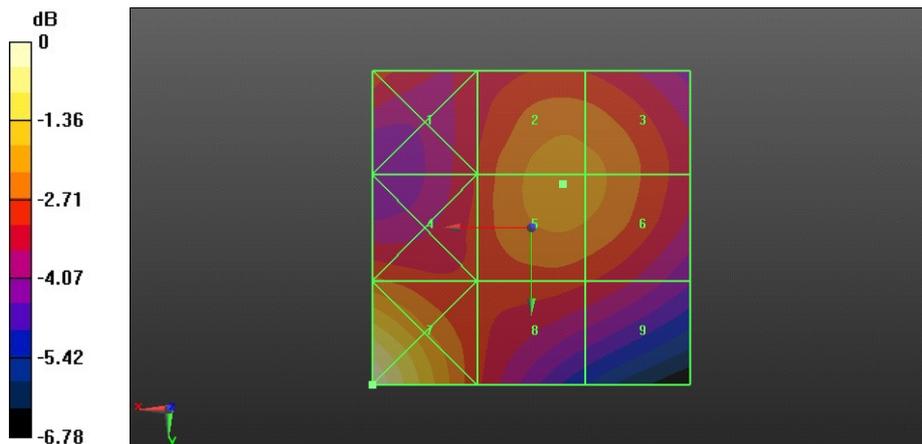
Grid 1 M3 0.171 A/m	Grid 2 M3 0.186 A/m	Grid 3 M3 0.184 A/m
Grid 4 M3 0.175 A/m	Grid 5 M3 0.186 A/m	Grid 6 M3 0.185 A/m
Grid 7 M3 0.234 A/m	Grid 8 M3 0.168 A/m	Grid 9 M3 0.164 A/m

Cursor:

Total = 0.2345 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.2345 A/m = -12.60 dB(A/m)

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-GSM1900-512CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-GSM\GPRS\EGPRS-1TS; Frequency: 1850.2 MHz;Duty Cycle: 1:8.30042

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.07000 A/m; Power Drift = 0.07 dB

PMF = 2.830 is applied.

H-field emissions = 0.1809 A/m

Near-field category: M3 (AWF -5 dB)

PMF scaled H-field

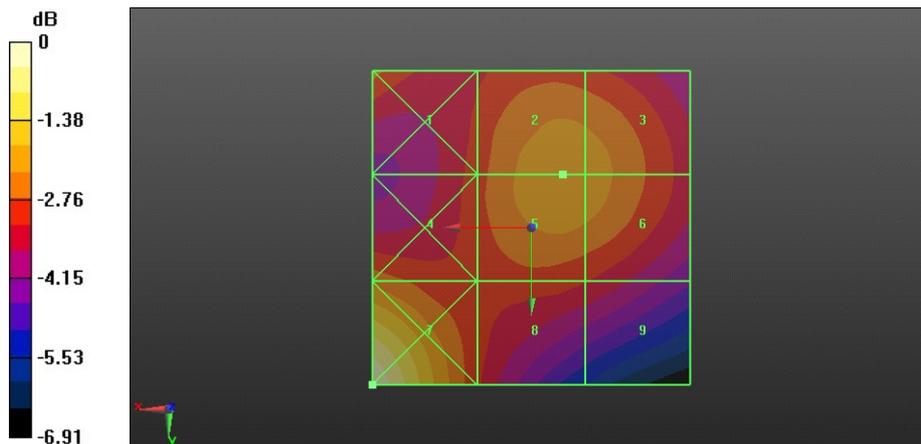
Grid 1 M3 0.170 A/m	Grid 2 M3 0.181 A/m	Grid 3 M3 0.179 A/m
Grid 4 M3 0.172 A/m	Grid 5 M3 0.181 A/m	Grid 6 M3 0.179 A/m
Grid 7 M3 0.227 A/m	Grid 8 M3 0.161 A/m	Grid 9 M3 0.157 A/m

Cursor:

Total = 0.2268 A/m

H Category: M3

Location: 25, 25, 8.7 mm



0 dB = 0.2268 A/m = -12.89 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band II-9538CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz; Duty Cycle: 1:1
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

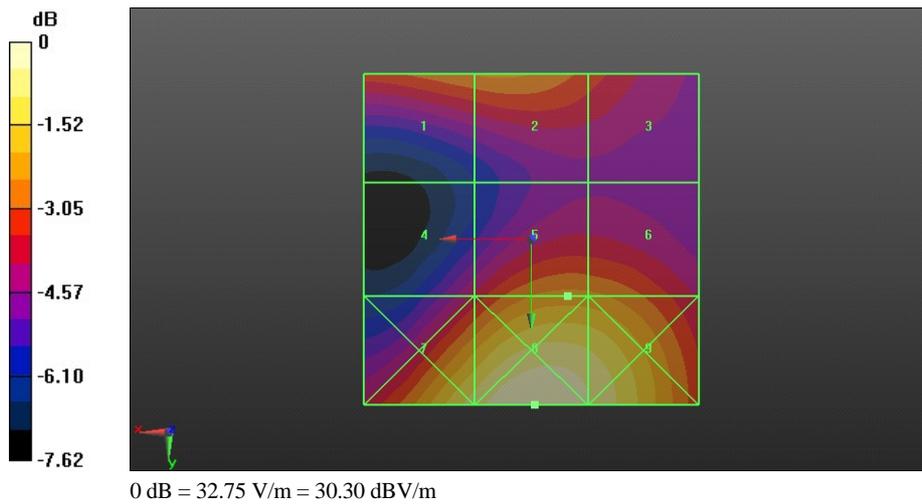
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 23.39 V/m; Power Drift = -0.00 dB
 PMF = 1.020 is applied.
 E-field emissions = 25.05 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 24.62 V/m	Grid 2 M4 24.84 V/m	Grid 3 M4 22.54 V/m
Grid 4 M4 20.88 V/m	Grid 5 M4 25.05 V/m	Grid 6 M4 24.89 V/m
Grid 7 M4 30.19 V/m	Grid 8 M4 32.75 V/m	Grid 9 M4 31.01 V/m

Cursor:
 Total = 32.75 V/m
 E Category: M4
 Location: -0.5, 25, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band II-9400CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 25.16 V/m; Power Drift = -0.04 dB

PMF = 1.020 is applied.

E-field emissions = 27.93 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

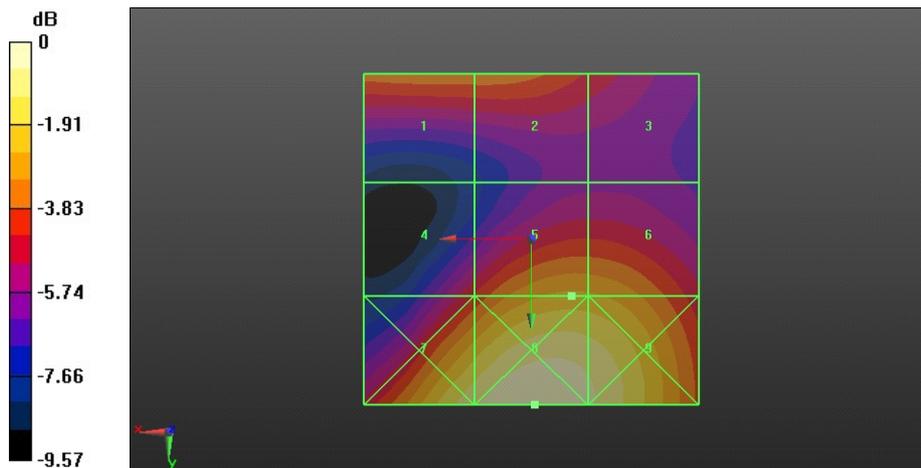
Grid 1 M4 25.09 V/m	Grid 2 M4 25.02 V/m	Grid 3 M4 21.81 V/m
Grid 4 M4 22.19 V/m	Grid 5 M4 27.93 V/m	Grid 6 M4 27.76 V/m
Grid 7 M4 33.79 V/m	Grid 8 M4 36.72 V/m	Grid 9 M4 34.61 V/m

Cursor:

Total = 36.72 V/m

E Category: M4

Location: -0.5, 25, 8.7 mm



0 dB = 36.72 V/m = 31.30 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band II-9262CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz;Duty Cycle: 1:1
 Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³
 Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

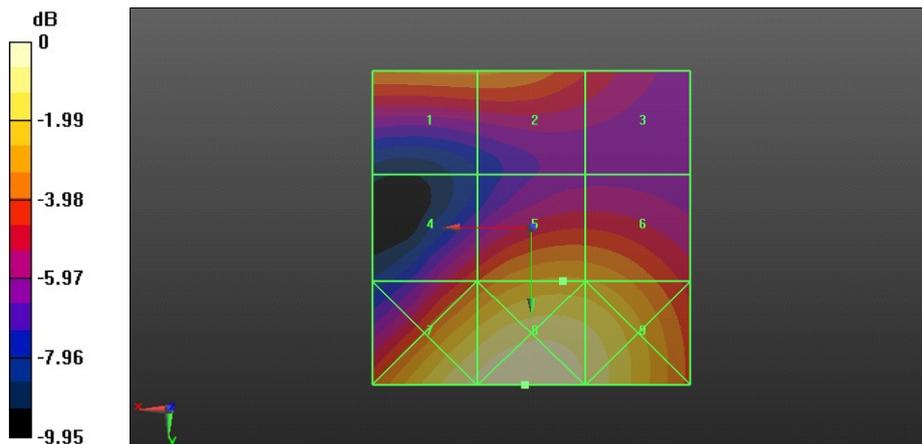
Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm
 Reference Value = 27.51 V/m; Power Drift = -0.19 dB
 PMF = 1.020 is applied.
 E-field emissions = 30.00 V/m
Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

Grid 1 M4 27.86 V/m	Grid 2 M4 27.82 V/m	Grid 3 M4 23.57 V/m
Grid 4 M4 25.18 V/m	Grid 5 M4 30.00 V/m	Grid 6 M4 29.67 V/m
Grid 7 M4 38.04 V/m	Grid 8 M4 39.81 V/m	Grid 9 M4 36.59 V/m

Cursor:
 Total = 39.81 V/m
 E Category: M4
 Location: 1, 25, 8.7 mm



0 dB = 39.81 V/m = 32.00 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band II-9262CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 28.65 V/m; Power Drift = 0.00 dB

PMF = 1.020 is applied.

E-field emissions = 30.99 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

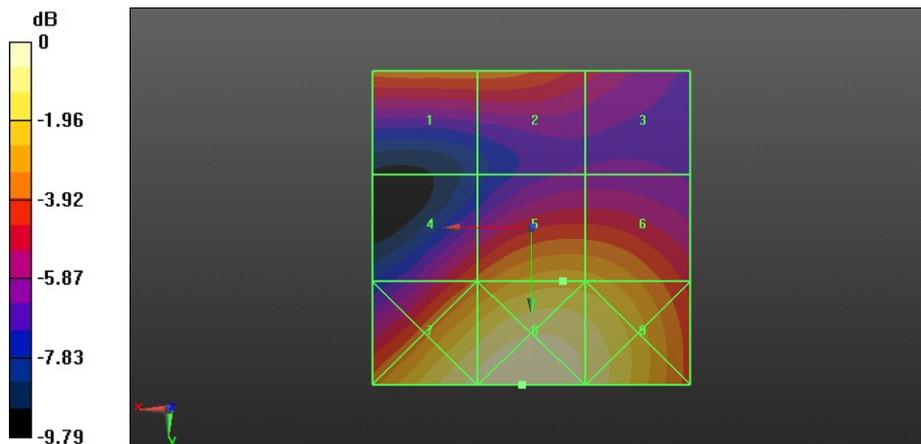
Grid 1 M4 26.76 V/m	Grid 2 M4 26.70 V/m	Grid 3 M4 22.78 V/m
Grid 4 M4 26.08 V/m	Grid 5 M4 30.99 V/m	Grid 6 M4 30.61 V/m
Grid 7 M4 38.06 V/m	Grid 8 M4 39.80 V/m	Grid 9 M4 36.58 V/m

Cursor:

Total = 39.80 V/m

E Category: M4

Location: 1.5, 25, 8.7 mm



0 dB = 39.80 V/m = 32.00 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band II-9538CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1907.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08100 A/m; Power Drift = -0.02 dB

PMF = 1.010 is applied.

H-field emissions = 0.07470 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

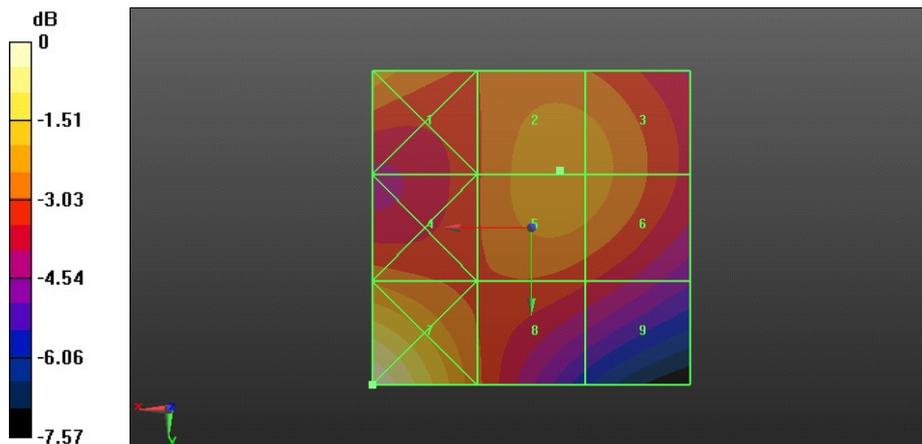
Grid 1 M4 0.075 A/m	Grid 2 M4 0.075 A/m	Grid 3 M4 0.074 A/m
Grid 4 M4 0.071 A/m	Grid 5 M4 0.075 A/m	Grid 6 M4 0.074 A/m
Grid 7 M4 0.096 A/m	Grid 8 M4 0.069 A/m	Grid 9 M4 0.064 A/m

Cursor:

Total = 0.09561 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.09561 A/m = -20.39 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band II-9400CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1880 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08200 A/m; Power Drift = 0.02 dB

PMF = 1.010 is applied.

H-field emissions = 0.07606 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

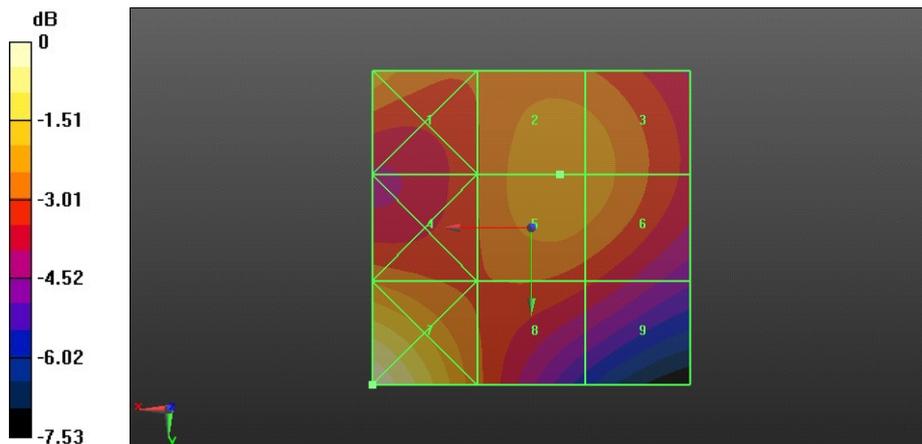
Grid 1 M4 0.076 A/m	Grid 2 M4 0.076 A/m	Grid 3 M4 0.075 A/m
Grid 4 M4 0.072 A/m	Grid 5 M4 0.076 A/m	Grid 6 M4 0.075 A/m
Grid 7 M4 0.097 A/m	Grid 8 M4 0.070 A/m	Grid 9 M4 0.066 A/m

Cursor:

Total = 0.09664 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.09664 A/m = -20.30 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band II-9262CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.08400 A/m; Power Drift = 0.01 dB

PMF = 1.010 is applied.

H-field emissions = 0.07694 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

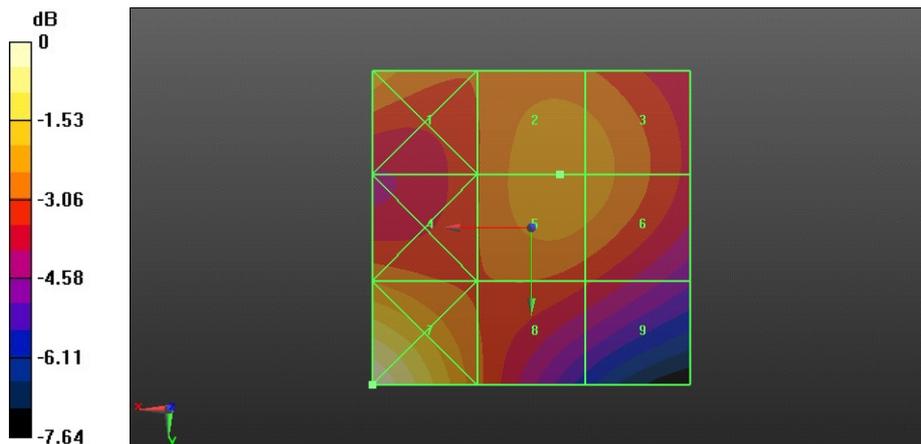
Grid 1 M4 0.077 A/m	Grid 2 M4 0.077 A/m	Grid 3 M4 0.076 A/m
Grid 4 M4 0.073 A/m	Grid 5 M4 0.077 A/m	Grid 6 M4 0.076 A/m
Grid 7 M4 0.098 A/m	Grid 8 M4 0.071 A/m	Grid 9 M4 0.066 A/m

Cursor:

Total = 0.09830 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.09830 A/m = -20.15 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band II-9262CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1852.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.09600 A/m; Power Drift = 0.02 dB

PMF = 1.010 is applied.

H-field emissions = 0.08830 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

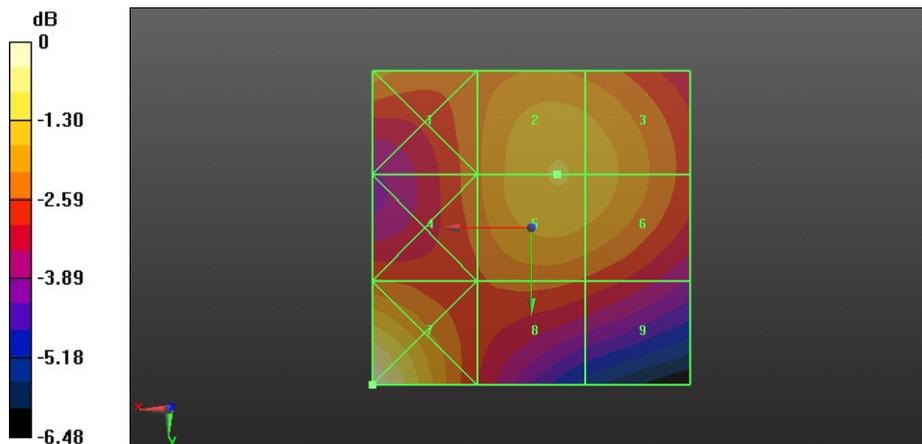
Grid 1 M4 0.083 A/m	Grid 2 M4 0.088 A/m	Grid 3 M4 0.087 A/m
Grid 4 M4 0.079 A/m	Grid 5 M4 0.088 A/m	Grid 6 M4 0.087 A/m
Grid 7 M4 0.102 A/m	Grid 8 M4 0.077 A/m	Grid 9 M4 0.075 A/m

Cursor:

Total = 0.1023 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1023 A/m = -19.80 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band IV-1513CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.61 V/m; Power Drift = -0.04 dB

PMF = 1.020 is applied.

E-field emissions = 33.91 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

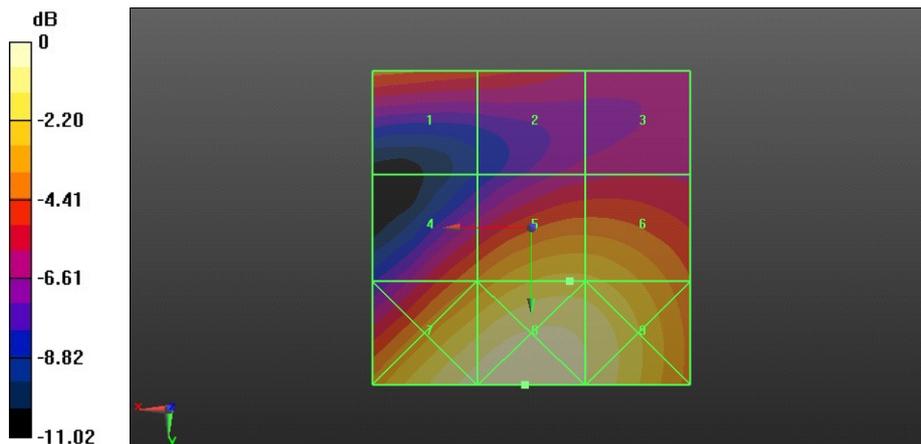
Grid 1 M4 26.47 V/m	Grid 2 M4 24.58 V/m	Grid 3 M4 21.50 V/m
Grid 4 M4 28.09 V/m	Grid 5 M4 33.91 V/m	Grid 6 M4 33.65 V/m
Grid 7 M4 40.54 V/m	Grid 8 M4 42.28 V/m	Grid 9 M4 39.13 V/m

Cursor:

Total = 42.28 V/m

E Category: M4

Location: 1, 25, 8.7 mm



0 dB = 42.28 V/m = 32.52 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band IV-1413CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 31.77 V/m; Power Drift = 0.06 dB

PMF = 1.020 is applied.

E-field emissions = 35.53 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

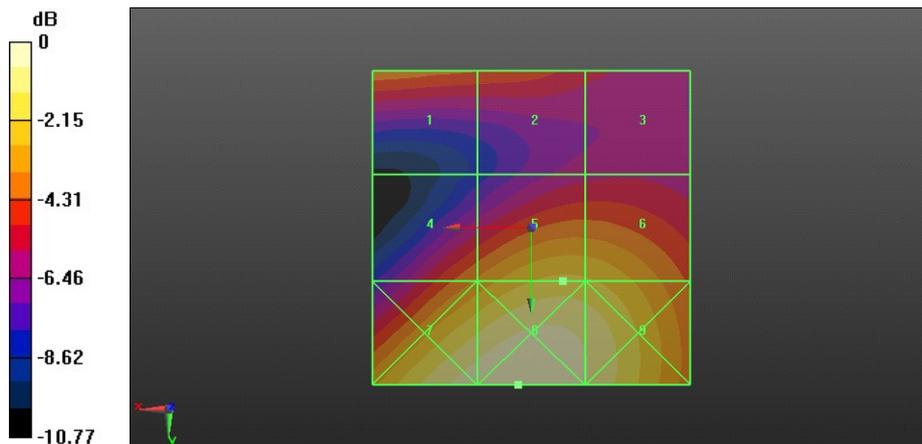
Grid 1 M4 28.92 V/m	Grid 2 M4 27.26 V/m	Grid 3 M4 23.89 V/m
Grid 4 M4 29.91 V/m	Grid 5 M4 35.53 V/m	Grid 6 M4 35.14 V/m
Grid 7 M4 43.06 V/m	Grid 8 M4 44.31 V/m	Grid 9 M4 41.12 V/m

Cursor:

Total = 44.31 V/m

E Category: M4

Location: 2, 25, 8.7 mm



0 dB = 44.31 V/m = 32.93 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band IV-1312CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SARI

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 30.30 V/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

E-field emissions = 34.70 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

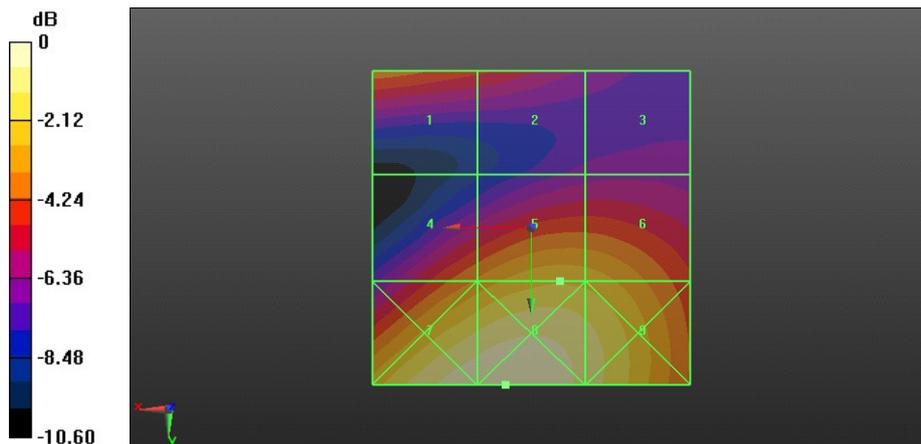
Grid 1 M4 29.06 V/m	Grid 2 M4 26.05 V/m	Grid 3 M4 21.36 V/m
Grid 4 M4 30.38 V/m	Grid 5 M4 34.70 V/m	Grid 6 M4 34.17 V/m
Grid 7 M4 44.17 V/m	Grid 8 M4 44.73 V/m	Grid 9 M4 40.04 V/m

Cursor:

Total = 44.73 V/m

E Category: M4

Location: 4, 25, 8.7 mm



0 dB = 44.73 V/m = 33.01 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band IV-1413CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 36.02 V/m; Power Drift = -0.01 dB

PMF = 1.020 is applied.

E-field emissions = 37.86 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

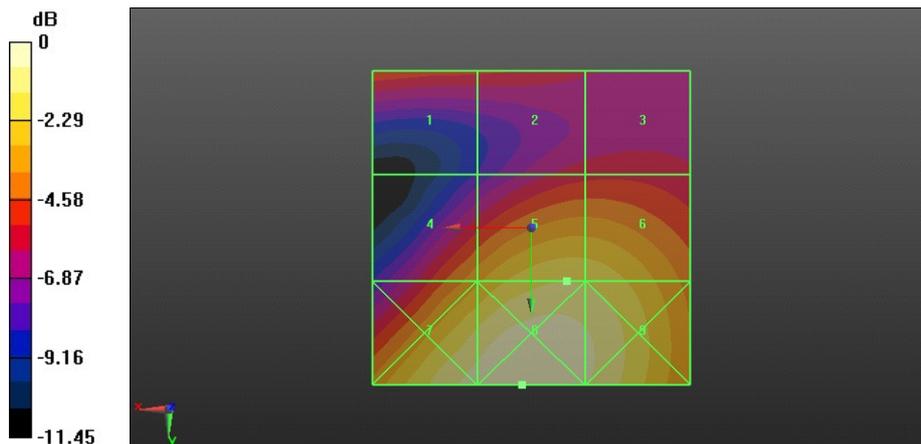
Grid 1 M4 26.57 V/m	Grid 2 M4 25.24 V/m	Grid 3 M4 23.97 V/m
Grid 4 M4 31.20 V/m	Grid 5 M4 37.86 V/m	Grid 6 M4 37.53 V/m
Grid 7 M4 43.18 V/m	Grid 8 M4 45.15 V/m	Grid 9 M4 42.21 V/m

Cursor:

Total = 45.15 V/m

E Category: M4

Location: 1.5, 25, 8.7 mm



0 dB = 45.15 V/m = 33.09 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band IV-1513CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1752.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1050 A/m; Power Drift = 0.07 dB

PMF = 0.9800 is applied.

H-field emissions = 0.09530 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

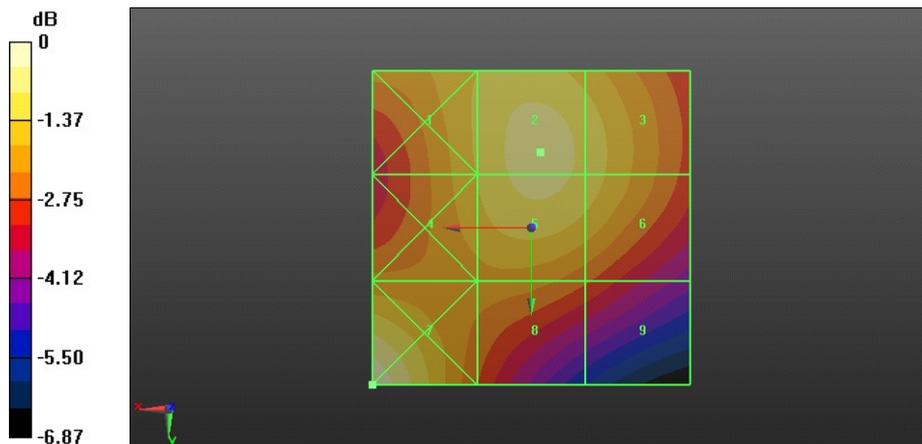
Grid 1 M4 0.089 A/m	Grid 2 M4 0.095 A/m	Grid 3 M4 0.092 A/m
Grid 4 M4 0.089 A/m	Grid 5 M4 0.095 A/m	Grid 6 M4 0.091 A/m
Grid 7 M4 0.104 A/m	Grid 8 M4 0.082 A/m	Grid 9 M4 0.076 A/m

Cursor:

Total = 0.1036 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1036 A/m = -19.69 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band IV-1413CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1160 A/m; Power Drift = 0.06 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1050 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

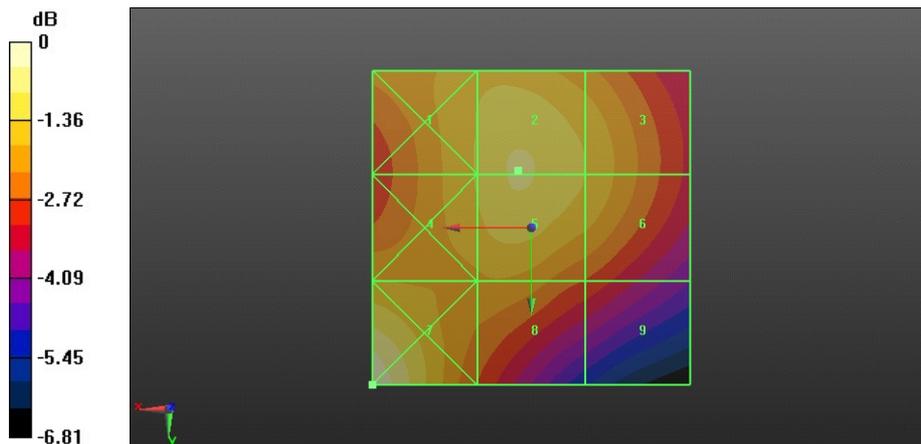
Grid 1 M4 0.100 A/m	Grid 2 M4 0.105 A/m	Grid 3 M4 0.099 A/m
Grid 4 M4 0.100 A/m	Grid 5 M4 0.105 A/m	Grid 6 M4 0.099 A/m
Grid 7 M4 0.116 A/m	Grid 8 M4 0.094 A/m	Grid 9 M4 0.085 A/m

Cursor:

Total = 0.1160 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1160 A/m = -18.71 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band IV-1312CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1712.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1150 A/m; Power Drift = -0.05 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1036 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

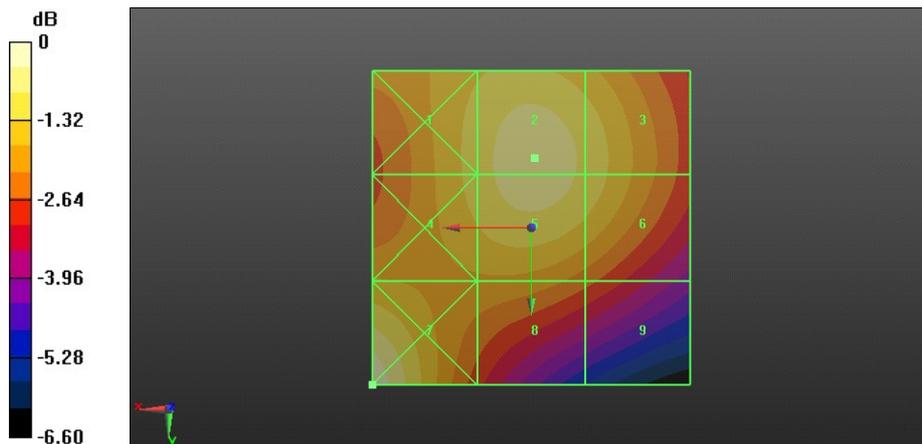
Grid 1 M4 0.098 A/m	Grid 2 M4 0.104 A/m	Grid 3 M4 0.100 A/m
Grid 4 M4 0.098 A/m	Grid 5 M4 0.103 A/m	Grid 6 M4 0.099 A/m
Grid 7 M4 0.112 A/m	Grid 8 M4 0.090 A/m	Grid 9 M4 0.084 A/m

Cursor:

Total = 0.1115 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1115 A/m = -19.05 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band IV-1413CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 1732.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.1160 A/m; Power Drift = 0.03 dB

PMF = 0.9800 is applied.

H-field emissions = 0.1038 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

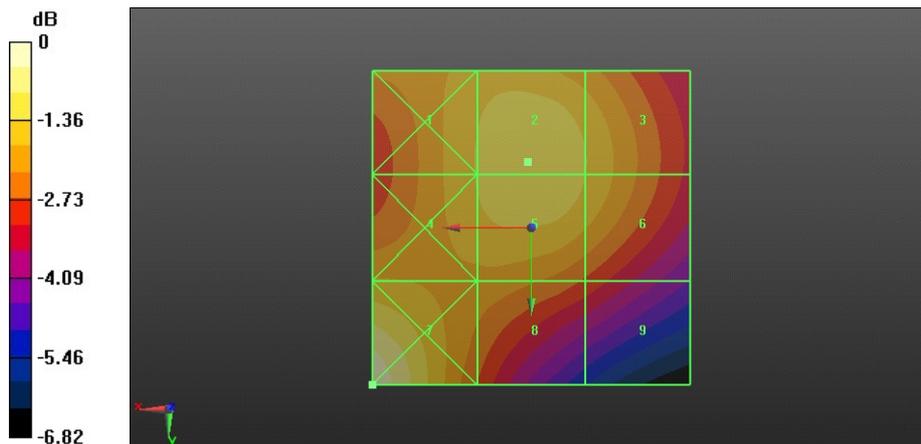
Grid 1 M4 0.100 A/m	Grid 2 M4 0.104 A/m	Grid 3 M4 0.100 A/m
Grid 4 M4 0.100 A/m	Grid 5 M4 0.104 A/m	Grid 6 M4 0.099 A/m
Grid 7 M4 0.116 A/m	Grid 8 M4 0.093 A/m	Grid 9 M4 0.084 A/m

Cursor:

Total = 0.1162 A/m

H Category: M4

Location: 25, 25, 8.7 mm



0 dB = 0.1162 A/m = -18.70 dB/A/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band V-4233CH**DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 88.89 V/m; Power Drift = -0.01 dB

PMF = 1.040 is applied.

E-field emissions = 72.17 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

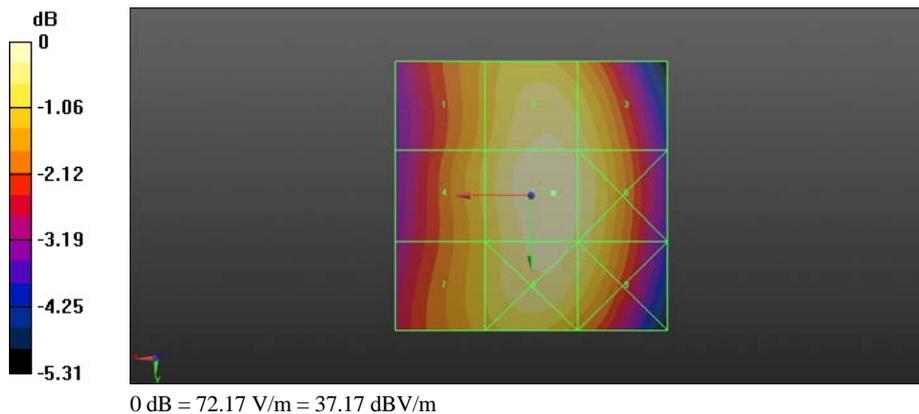
Grid 1 M4 63.54 V/m	Grid 2 M4 70.28 V/m	Grid 3 M4 68.49 V/m
Grid 4 M4 64.90 V/m	Grid 5 M4 72.17 V/m	Grid 6 M4 70.09 V/m
Grid 7 M4 64.05 V/m	Grid 8 M4 70.54 V/m	Grid 9 M4 68.64 V/m

Cursor:

Total = 72.17 V/m

E Category: M4

Location: -4, -0.5, 8.7 mm



Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band V-4182CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 85.22 V/m; Power Drift = 0.01 dB

PMF = 1.040 is applied.

E-field emissions = 68.93 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

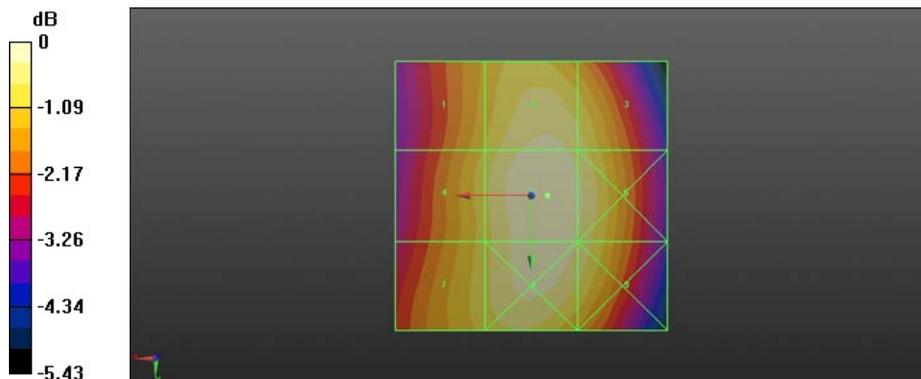
Grid 1 M4 61.27 V/m	Grid 2 M4 67.13 V/m	Grid 3 M4 64.99 V/m
Grid 4 M4 62.84 V/m	Grid 5 M4 68.93 V/m	Grid 6 M4 66.90 V/m
Grid 7 M4 62.77 V/m	Grid 8 M4 68.19 V/m	Grid 9 M4 65.89 V/m

Cursor:

Total = 68.93 V/m

E Category: M4

Location: -3, 0, 8.7 mm



0 dB = 68.93 V/m = 36.77 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band V-4132CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 85.28 V/m; Power Drift = -0.03 dB

PMF = 1.040 is applied.

E-field emissions = 68.61 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

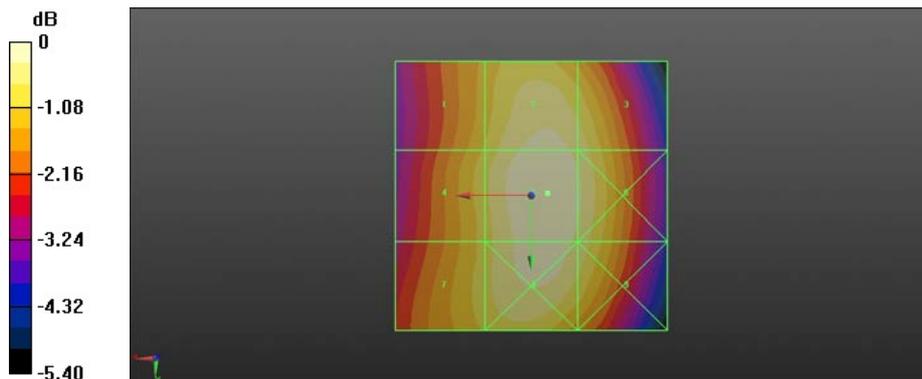
Grid 1 M4 61.08 V/m	Grid 2 M4 67.06 V/m	Grid 3 M4 64.95 V/m
Grid 4 M4 62.58 V/m	Grid 5 M4 68.61 V/m	Grid 6 M4 66.42 V/m
Grid 7 M4 62.25 V/m	Grid 8 M4 67.52 V/m	Grid 9 M4 65.14 V/m

Cursor:

Total = 68.61 V/m

E Category: M4

Location: -3, -0.5, 8.7 mm



0 dB = 68.61 V/m = 36.73 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_ER3DV6_H867G-UMTS Band V-4233CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: ER3DV6 - SN2480; ConvF(1, 1, 1); Calibrated: 2012-1-4;
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device E-Field measurement (E-field scan for ANSI C63.19-2007 compliance)/E Scan - ER3D: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1); Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 89.50 V/m; Power Drift = -0.04 dB

PMF = 1.040 is applied.

E-field emissions = 71.86 V/m

Near-field category: M4 (AWF 0 dB)

PMF scaled E-field

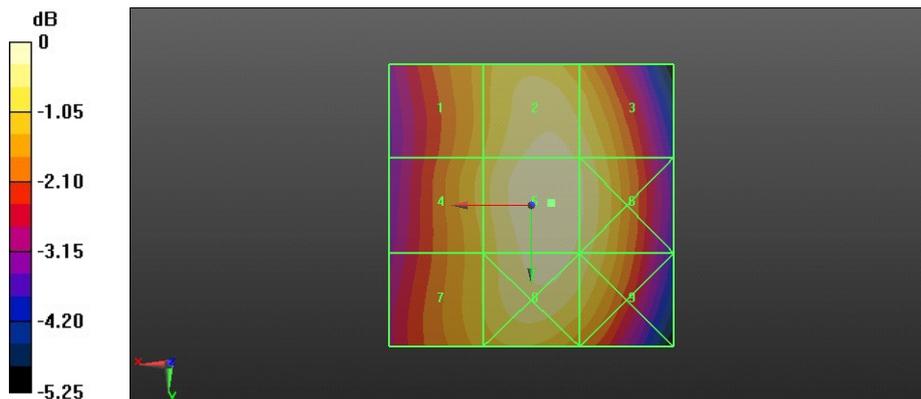
Grid 1 M4 63.80 V/m	Grid 2 M4 70.35 V/m	Grid 3 M4 68.47 V/m
Grid 4 M4 65.13 V/m	Grid 5 M4 71.86 V/m	Grid 6 M4 69.62 V/m
Grid 7 M4 63.98 V/m	Grid 8 M4 70.36 V/m	Grid 9 M4 68.21 V/m

Cursor:

Total = 71.86 V/m

E Category: M4

Location: -3.5, -0.5, 8.7 mm



0 dB = 71.86 V/m = 37.13 dBV/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band V-4233CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06700 A/m; Power Drift = 0.05 dB

PMF = 1.020 is applied.

H-field emissions = 0.09528 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

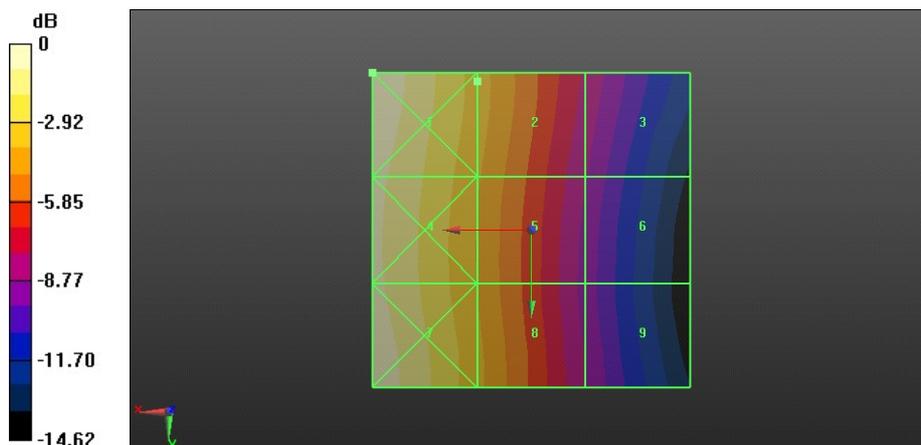
Grid 1 M4 0.140 A/m	Grid 2 M4 0.095 A/m	Grid 3 M4 0.056 A/m
Grid 4 M4 0.131 A/m	Grid 5 M4 0.091 A/m	Grid 6 M4 0.052 A/m
Grid 7 M4 0.137 A/m	Grid 8 M4 0.093 A/m	Grid 9 M4 0.052 A/m

Cursor:

Total = 0.1404 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1404 A/m = -17.05 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band V-4182CH

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth ; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 836.4 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06400 A/m; Power Drift = 0.01 dB

PMF = 1.020 is applied.

H-field emissions = 0.09236 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

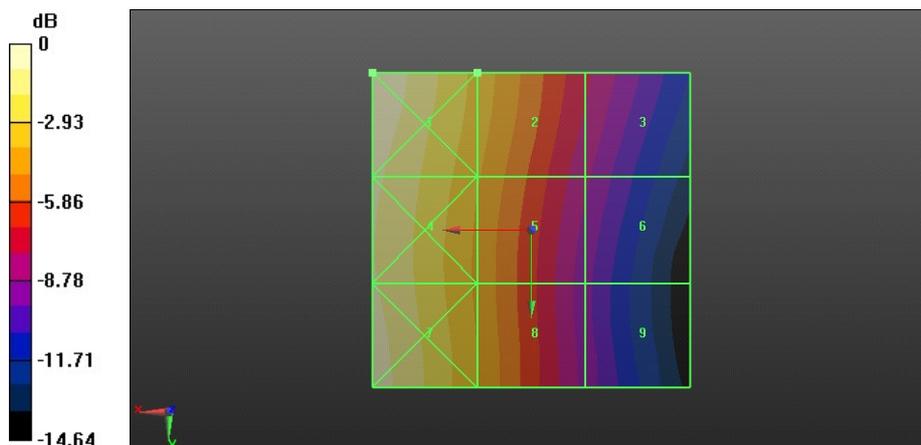
Grid 1 M4 0.134 A/m	Grid 2 M4 0.092 A/m	Grid 3 M4 0.056 A/m
Grid 4 M4 0.124 A/m	Grid 5 M4 0.087 A/m	Grid 6 M4 0.050 A/m
Grid 7 M4 0.128 A/m	Grid 8 M4 0.086 A/m	Grid 9 M4 0.047 A/m

Cursor:

Total = 0.1341 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1341 A/m = -17.45 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band V-4132CH**DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1**

Communication System: HW-UMTS-FDD; Frequency: 826.4 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), $z = 8.7$
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: $dx=0.5000$ mm, $dy=0.5000$ mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06300 A/m; Power Drift = -0.05 dB

PMF = 1.020 is applied.

H-field emissions = 0.08923 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

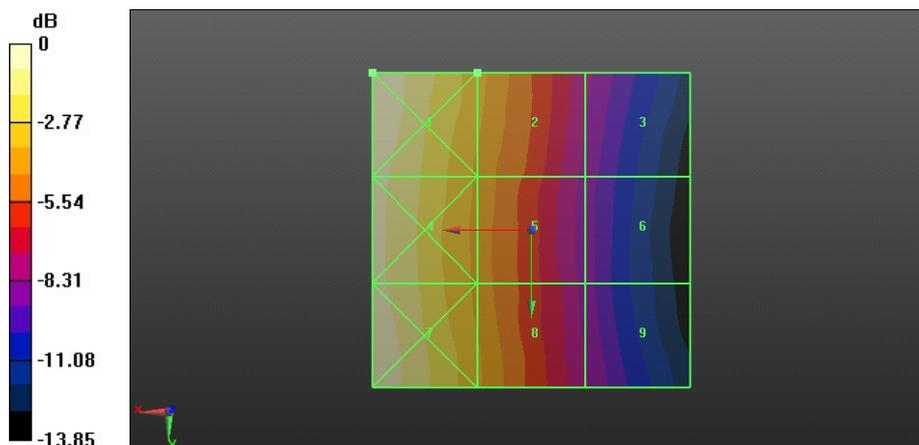
Grid 1 M4 0.131 A/m	Grid 2 M4 0.089 A/m	Grid 3 M4 0.052 A/m
Grid 4 M4 0.122 A/m	Grid 5 M4 0.084 A/m	Grid 6 M4 0.049 A/m
Grid 7 M4 0.127 A/m	Grid 8 M4 0.088 A/m	Grid 9 M4 0.051 A/m

Cursor:

Total = 0.1308 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1308 A/m = -17.67 dBA/m

Test Laboratory: HUAWEI SAR/HAC Lab

HAC_H3DV6_H867G-UMTS Band V-4132CH-2#

DUT: H867G; Type: HSPA/UMTS/GPRS/GSM/EDGE Mobile Phone with Bluetooth; Serial: SAR1

Communication System: HW-UMTS-FDD; Frequency: 846.6 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 0$ kg/m³

Phantom section: RF Section

DASY Configuration:

- Probe: H3DV6 - SN6305; ; Calibrated: 2012-1-4
- Sensor-Surface: (Fix Surface), z = 8.7
- Electronics: DAE4 Sn913; Calibrated: 2011-12-23
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1053
- DASY52 52.8.3(988); SEMCAD X 14.6.7(6848)

Device H-Field measurement with H3DV6 probe (H-field scan for ANSI C63.19-2007 compliance)/H Scan - H3DV6: 15 mm from Probe Center to the Device/Hearing Aid Compatibility Test (101x101x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 0.06900 A/m; Power Drift = 0.03 dB

PMF = 1.020 is applied.

H-field emissions = 0.09745 A/m

Near-field category: M4 (AWF 0 dB)

PMF scaled H-field

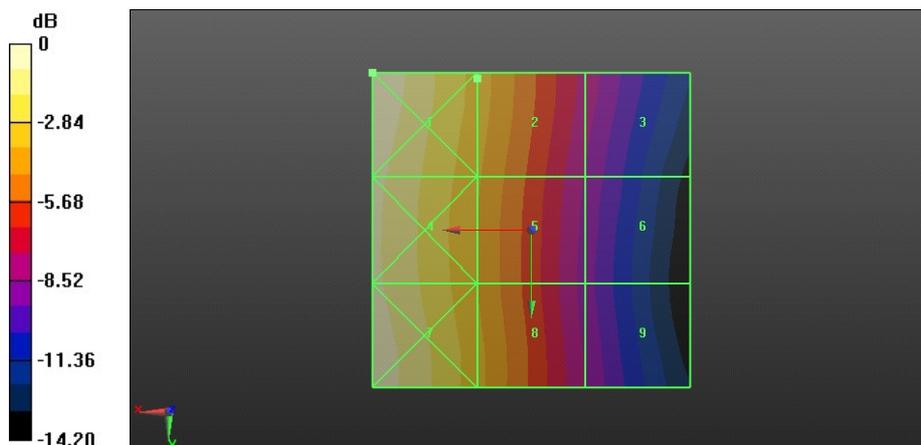
Grid 1 M4 0.142 A/m	Grid 2 M4 0.097 A/m	Grid 3 M4 0.057 A/m
Grid 4 M4 0.132 A/m	Grid 5 M4 0.093 A/m	Grid 6 M4 0.053 A/m
Grid 7 M4 0.138 A/m	Grid 8 M4 0.095 A/m	Grid 9 M4 0.053 A/m

Cursor:

Total = 0.1416 A/m

H Category: M4

Location: 25, -25, 8.7 mm



0 dB = 0.1416 A/m = -16.98 dBA/m